# 产品规格书

批 准	审 核	校 核	编 制
朴雨根	纪春华	朴致均	郑羿
2018. 04. 18	2018. 04. 18	2018. 04. 18	2018. 04. 18

#### 规格书更改履历:

序号	更改内容	履历号	更改时间	责任人
1	新规制定	000	2017. 10. 18	郑羿
2	增加决裁	001	2018. 04. 18	郑羿
3				

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# K2N7002K

**N-Channel Enhancement Mode MOSFET** 

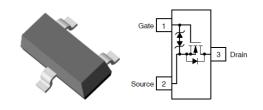
## **High Speed Switching Application**

#### **Features**

• ESD rating: 1000V (HBM)

• Low On-Resistance:  $R_{DS(on)}$  < 3 $\Omega$  @  $V_{GS}$  = 10V

- High power and current handling capability
- · Very fast switching
- · RoHS compliant device



#### SOT-23

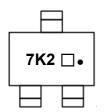
#### **Applications**

• High speed line driver

#### **Ordering Information**

Part Number	Marking Code	Package	Packaging
K2N7002K	7K2 □•	SOT-23	Tape & Reel

#### **Marking Information**



7K2 = Specific Device Code

☐ = Year & Week Code Marking

• = Dalian

#### **Absolute Maximum Ratings** (T<sub>amb</sub>=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Drain-Source voltage	$V_{DS}$	60	V
Gate-Source voltage	$V_{GS}$	±20	V
Maximum drain current (Note 1)	I <sub>D</sub>	300	mA
Pulsed drain current (Note 1)	I <sub>DP</sub>	800	mA
Power dissipation (Note 2)	P <sub>D</sub>	350	mW
Operating junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55 ~ 150	°C
Thermal resistance junction to ambient (Note 2)	R <sub>th(j-a)</sub>	350	°C/W

Note 1) Limited only maximum junction temperature

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Note 2) Device mounted on FR-4 board with recommended pad layout.

## K2N7002K

## **Electrical Characteristics** (T<sub>amb</sub>=25°C, Unless otherwise specified)

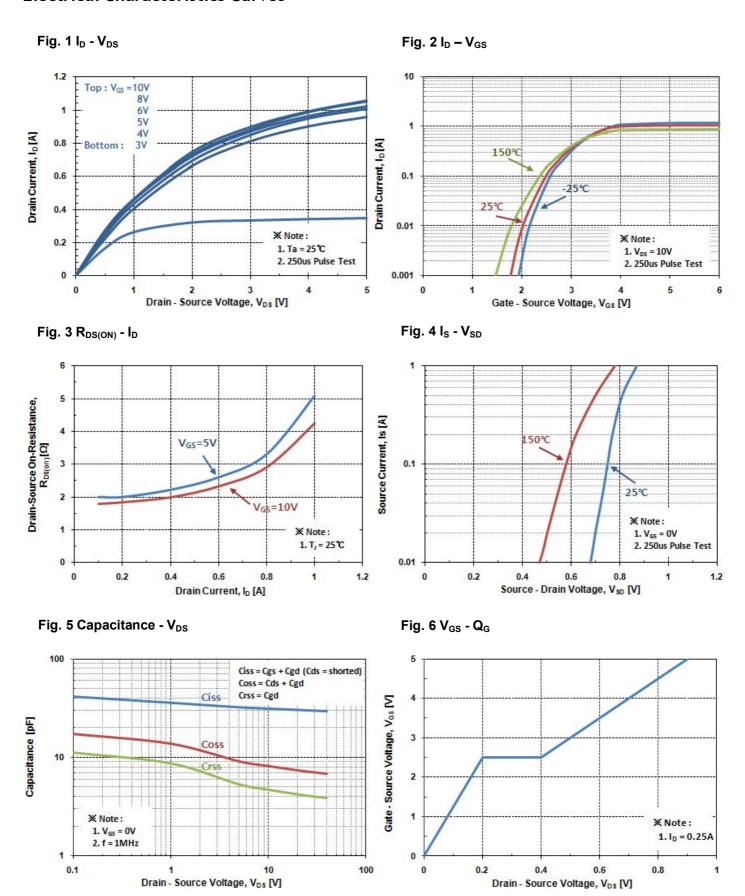
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Drian-Source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0	60	-	-	V
Gate-Source breakdown voltage	BV <sub>GSS</sub>	I <sub>G</sub> =250μA, V <sub>DS</sub> =0	±20	-	-	V
Gate-Threshold voltage	$V_{GS(th)}$	I <sub>D</sub> =250uA, V <sub>DS</sub> =V <sub>GS</sub>	1	-	2.5	V
Zero Gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0	-	-	1	μА
		V <sub>GS</sub> =±5V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate-body leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V			±150	nA
		V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±10	μΑ
Note 3)	_	V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A	-	-	3	Ω
Drain-Source on-resistance (Note 3)	$R_{DS(ON)}$	V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A	-	-	3.5	
Forward trans-conductance (Note 3)	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.2A	0.08	-	-	S
Input capacitance	C <sub>iss</sub>		-	30	50	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0, f=1MHz	-	7	-	pF
Reverse Transfer capacitance	C <sub>rss</sub>		-	4	-	
Turn-on delay time (Note 3, 4)	t <sub>d(on)</sub>		-	2	-	
Rise time (Note 3, 4)	t <sub>r</sub>	$V_{DD}$ =30V, $I_{D}$ =0.2A,	_	15	-	
Turn-off delay time (Note 3, 4)	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =10 $\Omega$		8	-	ns
Fall time (Note 3, 4)	t <sub>f</sub>		=	11	-	
Total gate charge (Note 3, 4)	$Q_g$		-	0.6	0.8	
Gate-Source charge (Note 3, 4)	$Q_{\mathrm{gs}}$	V <sub>DS</sub> =10V, I <sub>D</sub> =0.25A, V <sub>GS</sub> =4.5V	-	0.2	-	nC
Gate-Drain charge (Note 3, 4)	$Q_{gd}$	35	-	0.2	-	
Diode forward voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V, I <sub>S</sub> =0.2A	-	-	1.3	V

 $<sup>^{\</sup>text{Note 3})}$  Pulse test: Pulse width  $\leq\!300\text{us},\,\text{Duty cycle}\!\leq\!2\%$ 

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 $<sup>^{\</sup>text{Note 4})}$  Essentially independent of operating temperature typical characteristics.

#### **Electrical Characteristics Curves**

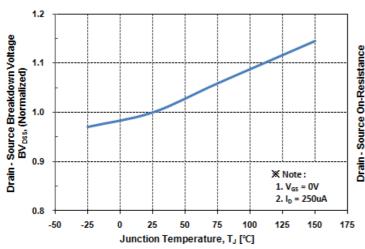


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## K2N7002K



Fig. 8 R<sub>DS(on)</sub> – T<sub>J</sub>



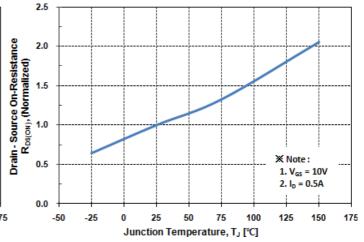
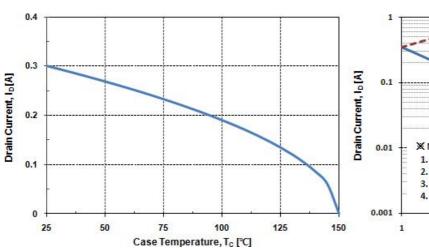


Fig. 9 I<sub>D</sub> - T<sub>C</sub>

Fig. 10 Safe Operating Area



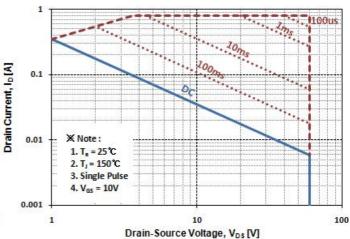
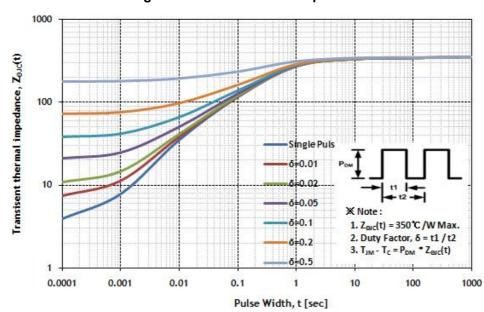
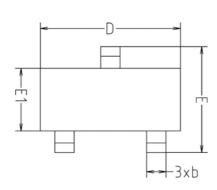


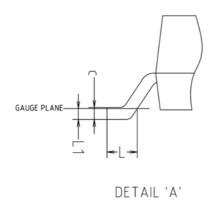
Fig. 11 Transient Thermal Impedance

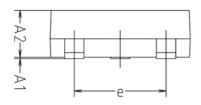


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## **Package Outline Dimensions**



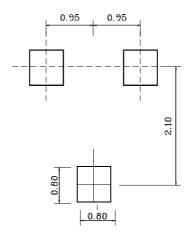






SYMBOL		NOTE		
3111000	MINIMUM	NOMINAL	MAXIMUM	NOTE
A1	0.00	-	0.10	
A2	0.82	-	1.02	
Ь	0.39	0.42	0.45	
С	0.09	0.12	0.15	
D	2.80	2.90	3.00	
E	2.20	2.40	2.60	
E1	1.20	1.30	1.40	
е	1.90BSC			
L	0.20	-	-	
L1	0.12BSC			

#### **X Recommend PCB solder land (Unit: mm)**



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